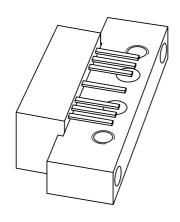
DISCRETE SEMICONDUCTORS

DATA SHEET



BGD714750 MHz, 20.3 dB gain power doubler amplifier

Product specification Supersedes data of 2001 Oct 29 2001 Nov 02





750 MHz, 20.3 dB gain power doubler amplifier

BGD714

FEATURES

- · Excellent linearity
- · Extremely low noise
- Excellent return loss properties
- Silicon nitride passivation
- Rugged construction
- Gold metallization ensures excellent reliability.

APPLICATIONS

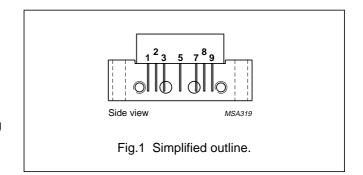
• CATV systems operating in the 40 to 750 MHz frequency range.

DESCRIPTION

Hybrid amplifier module in a SOT115J package operating with a voltage supply of 24 V (DC).

PINNING - SOT115J

PIN	DESCRIPTION	
1	input	
2, 3	common	
5	+V _B	
7, 8	common	
9	output	



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 45 MHz	20	20.6	dB
		f = 750 MHz	20.8	21.8	dB
I _{tot}	total current consumption (DC)	V _B = 24 V	380	410	mA

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER		MAX.	UNIT
V _B	supply voltage	_	30	V
Vi	RF input voltage	_	70	dBmV
T _{stg}	storage temperature		+100	°C
T _{mb}	operating mounting base temperature	-20	+100	°C

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CHARACTERISTICS

Bandwidth 40 to 750 MHz; V_B = 24 V; T_{mb} = 35 °C; Z_S = Z_L = 75 Ω

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Gp	power gain	f = 45 MHz	20	20.3	20.6	dB
		f = 750 MHz	20.8	21.3	21.8	dB
SL	slope straight line	f = 45 to 100 MHz; note 1	0.5	1	1.5	dB
FL	flatness straight line	f = 45 to 100 MHz	_	_	±0.35	dB
		f = 100 to 700 MHz	_	_	±0.5	dB
		f = 700 to 750 MHz	_	_	±0.15	dB
S ₁₁	input return losses	f = 45 to 80 MHz	23	_	_	dB
		f = 80 to 160 MHz	23	_	_	dB
		f = 160 to 320 MHz	21	_	_	dB
		f = 320 to 550 MHz	20	_	_	dB
		f = 550 to 650 MHz	20	_	_	dB
		f = 650 to 750 MHz	19	_	_	dB
		f = 750 to 790 MHz	17	_	_	dB
S ₂₂	output return losses	f = 45 to 80 MHz	23	_	_	dB
		f = 80 to 160 MHz	23	_	_	dB
		f = 160 to 320 MHz	20	_	_	dB
		f = 320 to 550 MHz	20	_	_	dB
		f = 550 to 650 MHz	20	_	_	dB
		f = 650 to 750 MHz	19	_	_	dB
		f = 750 to 790 MHz	17	_	_	dB
S ₂₁	phase response	f = 50 MHz	-45	_	+45	deg
СТВ	composite triple beat	112 channels flat; $V_0 = 44 \text{ dBmV}$; $f_m = 745.25 \text{ MHz}$	_	_	- 61	dB
		79 channels; $V_0 = 44 \text{ dBmV}$; $f_m = 547.25 \text{ MHz}$	_	_	-67	dB
		79 channels; f_m = 445.25 MHz; V_o = 49.3 dBmV at 547 MHz; note 2	_	_	-62	dB
X _{mod}	cross modulation	112 channels flat; $V_0 = 44 \text{ dBmV}$; $f_m = 55.25 \text{ MHz}$	_	_	-62	dB
		79 channels flat; $V_0 = 44 \text{ dBmV}$; $f_m = 55.25 \text{ MHz}$	_	_	-66	dB
		79 channels; f _m = 745.25 MHz; V _o = 49.3 dBmV at 547 MHz; note 2	_	_	-58	dB

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SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
CSO	composite second order distortion	112 channels flat; $V_o = 44 \text{ dBmV}$; $f_m = 746.5 \text{ MHz}$	_	_	-62	dB
		79 channels flat; $V_o = 44 \text{ dBmV}$; $f_m = 548.5 \text{ MHz}$	_	_	-67	dB
		79 channels; f_m = 746.5 MHz; V_o = 49.3 dBmV at 547 MHz; note 2	_	_	-60	dB
d ₂	second order distortion	note 3		_	-74	dB
Vo	output voltage	$d_{im} = -60 \text{ dB}$; note 4	64	_	_	dBmV
NF	noise figure	f = 50 MHz	_	_	5.5	dB
		f = 550 MHz	_	-	5.5	dB
		f = 750 MHz	_	_	7	dB
I _{tot}	total current consumption (DC)	note 5	380	395	410	mA

Notes

- 1. Slope straight line is defined as gain at 750 MHz gain at 45 MHz.
- 2. Tilt = 7.3 dB (55 to 547 MHz).
- $\begin{array}{ll} 3. & f_p = 55.25 \text{ MHz; V}_p = 44 \text{ dBmV;} \\ & f_q = 691.25 \text{ MHz; V}_q = 44 \text{ dBmV;} \\ & \text{measured at } f_p + f_q = 746.5 \text{ MHz.} \end{array}$
- 4. Measured according to DIN45004B:

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f_p = 740.25 \text{ MHz}; V_p = V_o;
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 $f_q = 747.25 \; MHz; \; V_q = V_o - 6 \; dB; \;$

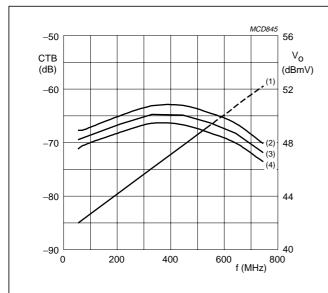
 $f_r = 749.25 \text{ MHz}; V_r = V_o - 6 \text{ dB};$

measured at $f_p + f_q - f_r = 738.25$ MHz.

5. The module normally operates at $V_B = 24 \text{ V}$, but is able to withstand supply transients up to 30 V.

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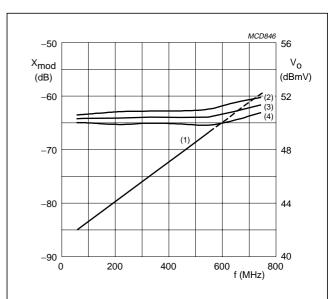
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 $Z_S = Z_L = 75~\Omega;~V_B = 24~V;~79~channels;\\ tilt = 7.3~dB~(50~to~550~MHz).$

- (1) V₀.
- (3) Typ.
- (2) Typ. +3 σ.
- (4) Typ. −3 σ.

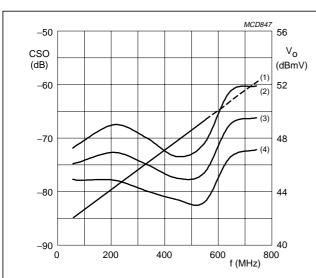
Fig.2 Composite triple beat as a function of frequency under tilted conditions.



 $Z_S = Z_L = 75~\Omega;~V_B = 24~V;~79~channels;\\ tilt = 7.3~dB~(50~to~550~MHz).$

- (1) V_o.
- (3) Typ.
- (2) Typ. +3 σ.
- (4) Typ. –3 σ.

Fig.3 Cross modulation as a function of frequency under tilted conditions.



 Z_S = Z_L = 75 $\Omega;~V_B$ = 24 V; 79 channels; tilt = 7.3 dB (50 to 550 MHz).

- (1) V_c
- (3) Typ.
- (2) Typ. +3 σ.
- (4) Typ. –3 σ.

Fig.4 Composite second order distortion as a function of frequency under tilted conditions.

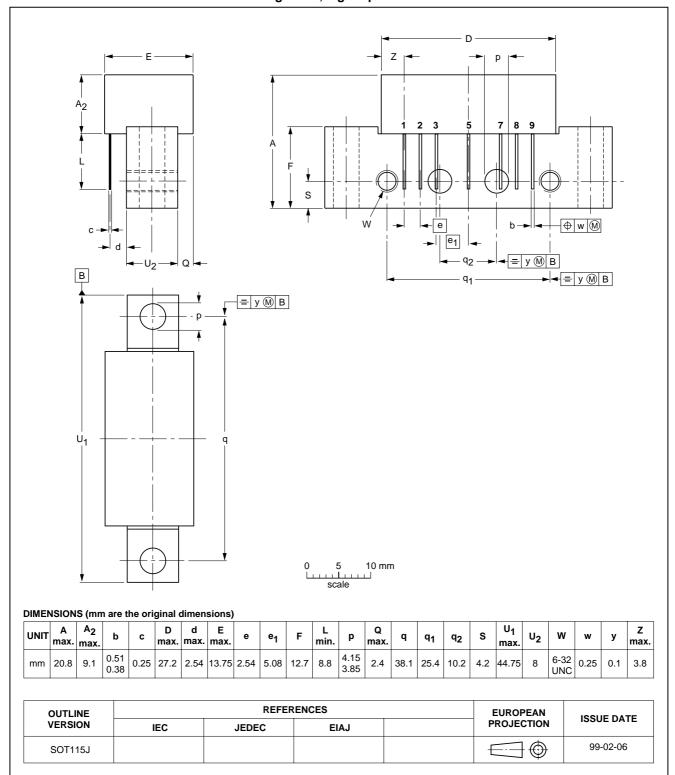
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PACKAGE OUTLINE

Rectangular single-ended package; aluminium flange; 2 vertical mounting holes; 2 x 6-32 UNC and 2 extra horizontal mounting holes; 7 gold-plated in-line leads

SOT115J



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DATA SHEET STATUS

DATA SHEET STATUS(1)	PRODUCT STATUS ⁽²⁾	DEFINITIONS
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Printed in The Netherlands

613518/04/pp8

Date of release: 2001 Nov 02

Document order number: 9397 750 09029

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